

FRAME TIMES

rate	frame time
TV	100/6 msec, doubly interlaced (synchronous)
RS	100/6 msec (synchronous)
S1	~0.7 sec
S2	~10 sec
F	~21 sec (synchronous)
Fx2	~42 sec (synchronous)
N	~85 sec (synchronous)
Nx2	~171 sec (synchronous)

BACKSCATTER YIELDS

(approximations for pseudo-amorphous samples)

beam axis coincident with sample normal:

$E_0 \geq 10$ keV:

$$\eta = -0.0254 + 0.016Z - 1.86 \times 10^{-4} Z^2 + 8.3 \times 10^{-7} Z^3$$

$1 \text{ keV} \geq E_0 \geq 40 \text{ keV}$:

$$\eta = E_0^m C \quad \text{where: } E_0 \text{ is in keV}$$

$$m = 0.1382 - 0.9211/Z^{0.5}$$

$$C = 0.1904 - 0.2235 \ln Z + 0.1292 (\ln Z)^2 - 0.01491 (\ln Z)^3$$

beam axis tilted significantly from sample normal:

$$\eta = 1/(1 + \cos \theta)^p, \quad p = 9/Z^{0.5}$$

E₂ CROSSOVERS for ASSORTED MATERIALS

kapton	400V	GaAs	2.6kV
UHMWPE	~800V	quartz	3.0kV
nylon	~1.2kV	Al ₂ O ₃	4.2kV
acetal	1.65kV		
PVC	1.65kV		
teflon	1.82kV		
glass (specific type)	~2kV		

most materials quoted from Scanning Electron Microscopy and X-Ray Microanalysis, 2nded

ELECTRON RANGE

$$R_{KO} = \frac{0.0276(A)E_0^{1.67}}{Z^{0.89}\rho} \mu\text{m}$$

Appreciable levels of backscatter contrast achieved from within approximately $0.3R_{KO}$ or less, but varies significantly with Z (deeper for low Z, shallower for high Z)